

Silicon PNP Power Transistors

2SB1087

DESCRIPTION

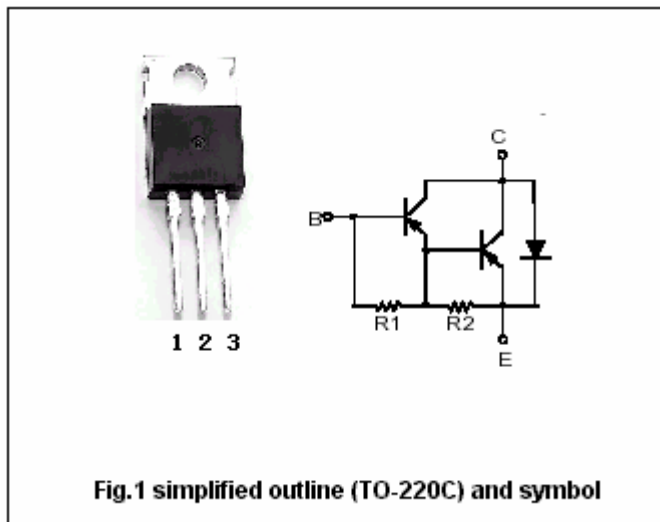
- With TO-220C package
- High DC current gain
- DARLINGTON

APPLICATIONS

- For low frequency power amplifier and low speed power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current-DC		-5	A
P _C	Collector power dissipation	T _a =25	1.5	W
		T _C =25	30	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-30mA, I _B =0	-100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A, I _B =-2mA			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2A, I _B =-2mA			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V, I _E =0			1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V, I _C =0			-3	mA
h _{FE-1}	DC current gain	I _C =-2A, V _{CE} =-5V	2000		20000	
h _{FE-2}	DC current gain	I _C =-5A, V _{CE} =-5V	500			

固电半导体

INCHANGE SEMICONDUCTOR

PACKAGE OUTLINE

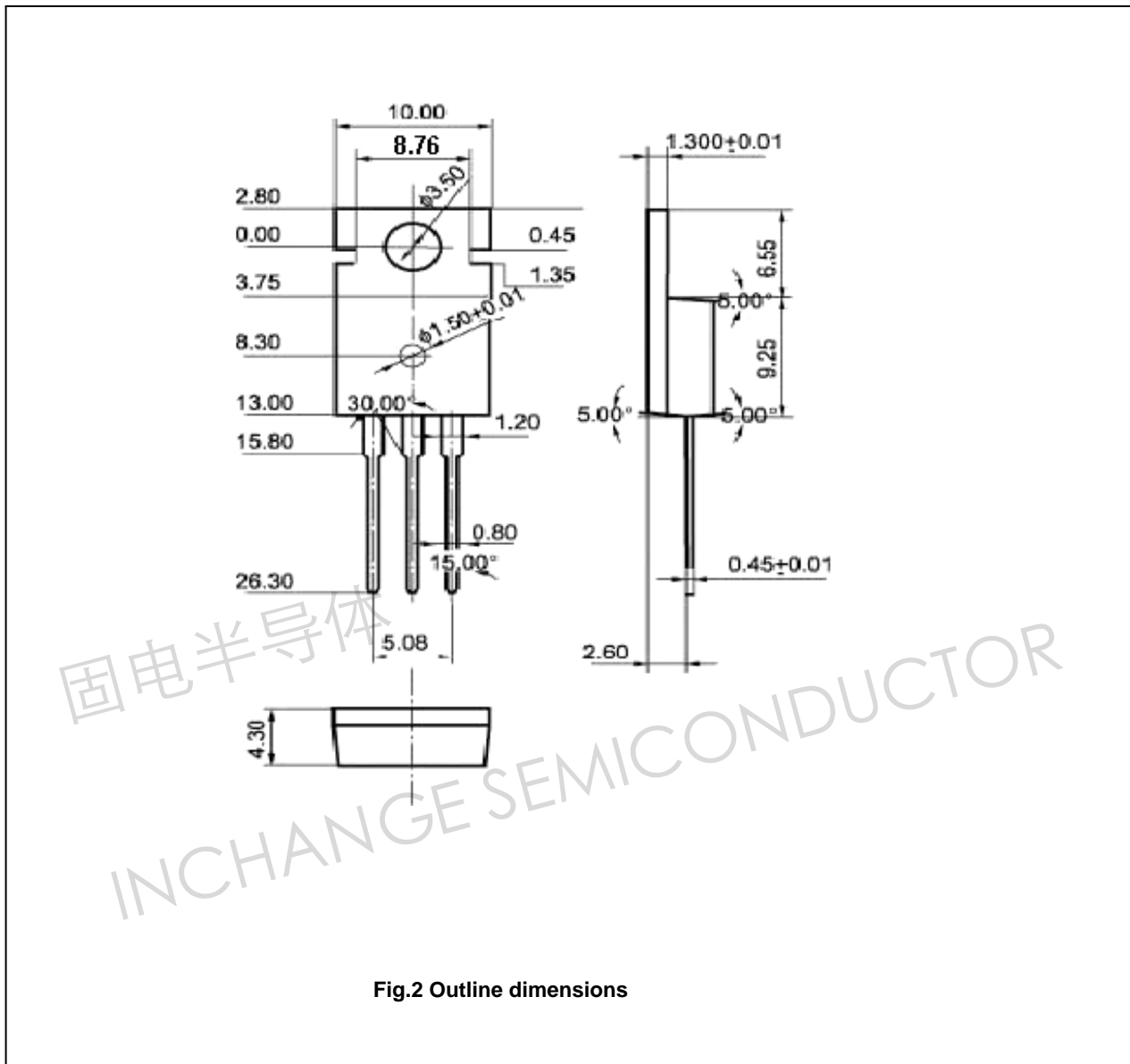


Fig.2 Outline dimensions